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BYC30X-600P

Hyperfast power diode

4 February 2013

Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_h \leq 51^\circ\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	30	A
Static characteristics						
V_F	forward voltage	$I_F = 30\text{ A}$; $T_j = 150^\circ\text{C}$; Fig. 6	-	1.38	1.8	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $dI_F/dt = 50\text{ A}/\mu\text{s}$; $T_j = 25^\circ\text{C}$; Fig. 7	-	-	35	ns



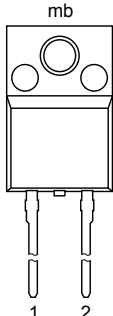
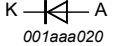
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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>TO-220F (SOD113)</p>	
2	A	anode		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC30X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC30X-600P	BYC30X-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_h \leq 51^\circ\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	30	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_h \leq 51^\circ\text{C}$; square-wave pulse	-	60	A

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Symbol	Parameter	Conditions	Min	Max	Unit
I_{FSM}	non-repetitive peak forward current	$t_p = 10 \text{ ms}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; sine-wave pulse; Fig. 4	-	200	A
		$t_p = 8.3 \text{ ms}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; sine-wave pulse; Fig. 4	-	220	A
T_{stg}	storage temperature		-65	175	$^\circ\text{C}$
T_j	junction temperature		-	175	$^\circ\text{C}$

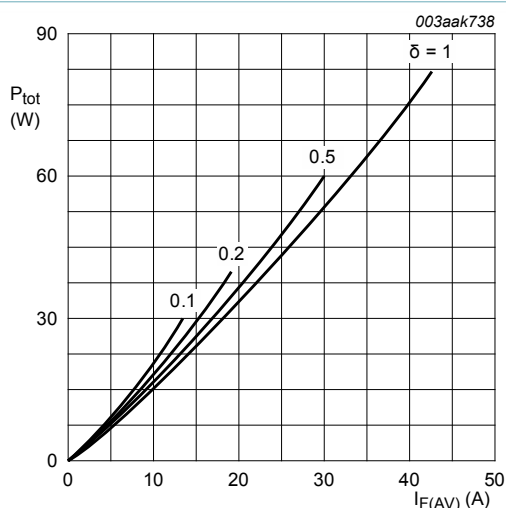


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_O = 1.798 \text{ V}; R_S = 0.003 \text{ } \Omega$$

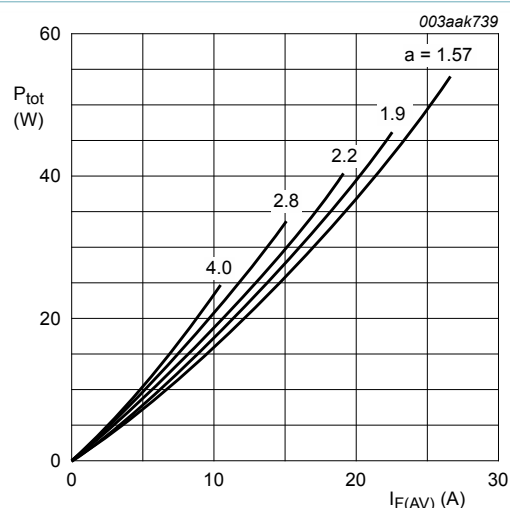


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_O = 1.798 \text{ V}; R_S = 0.003 \text{ } \Omega$$

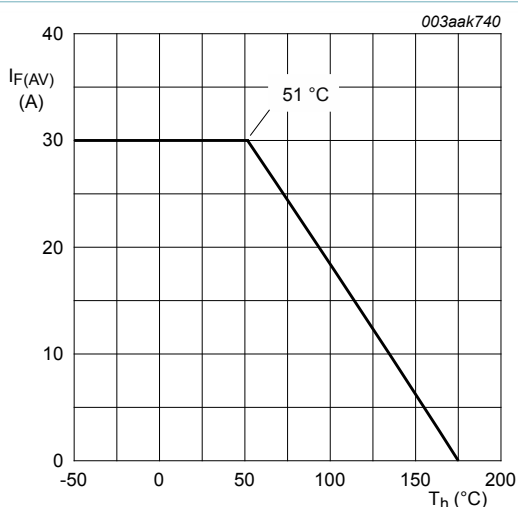


Fig. 3. Forward current as a function of heatsink temperature; maximum values

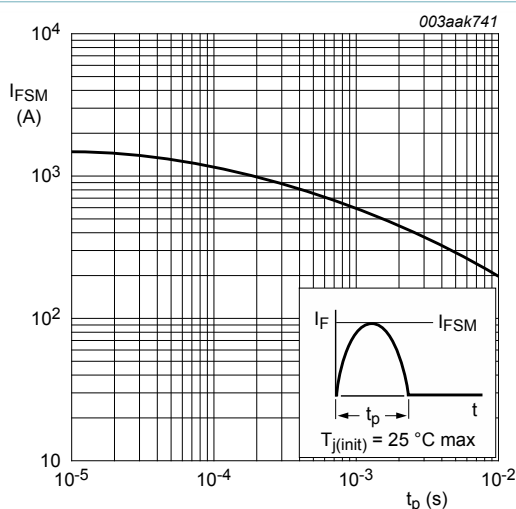


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound ; Fig. 5	-	-	3.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	55	-	K/W

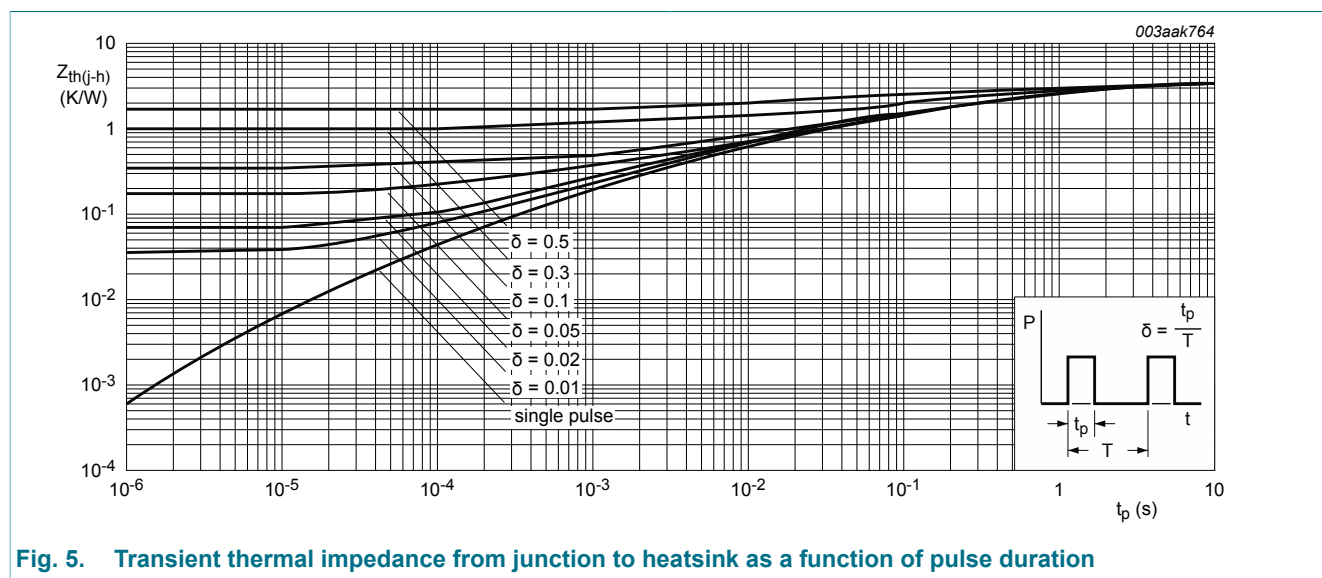


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 30$ A; $T_j = 25$ °C; Fig. 6	-	2	2.75	V

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$I_F = 30\text{ A}$; $T_j = 150\text{ }^{\circ}\text{C}$; Fig. 6		-	1.38	1.8	V
I_R	reverse current	$V_R = 600\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$		-	-	10	μA
		$V_R = 600\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$		-	-	600	μA
Dynamic characteristics							
Q_r	recovered charge	$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7		-	50	-	nC
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ }^{\circ}\text{C}$; Fig. 7		-	280	-	nC
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $dI_F/dt = 50\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7		-	-	35	ns
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7		-	-	35	ns
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ }^{\circ}\text{C}$; Fig. 7		-	70	-	ns
I_{RM}	peak reverse recovery current	$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7		-	3.5	-	A
		$I_F = 30\text{ A}$; $V_R = 200\text{ V}$; $dI_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ }^{\circ}\text{C}$; Fig. 7		-	7.6	-	A

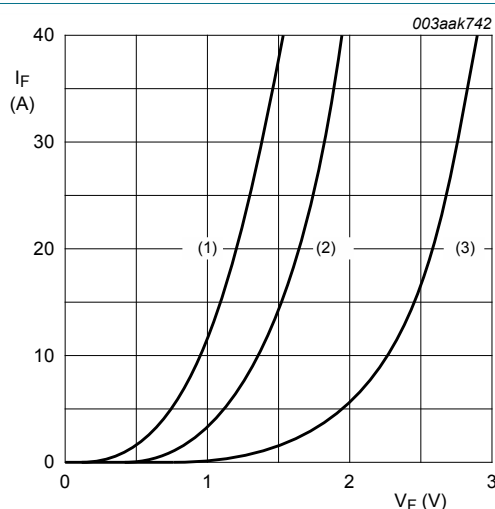


Fig. 6. Forward current as a function of forward voltage

- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values;
 - (2) $T_j = 150\text{ }^\circ\text{C}$; maximum values;
 - (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values;
- $V_O = 1.798\text{ V}$; $R_S = 0.003\text{ }\Omega$

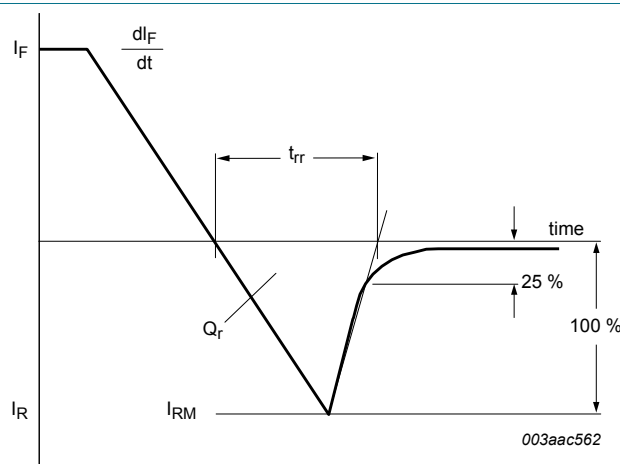


Fig. 7. Reverse recovery definitions; ramp recovery

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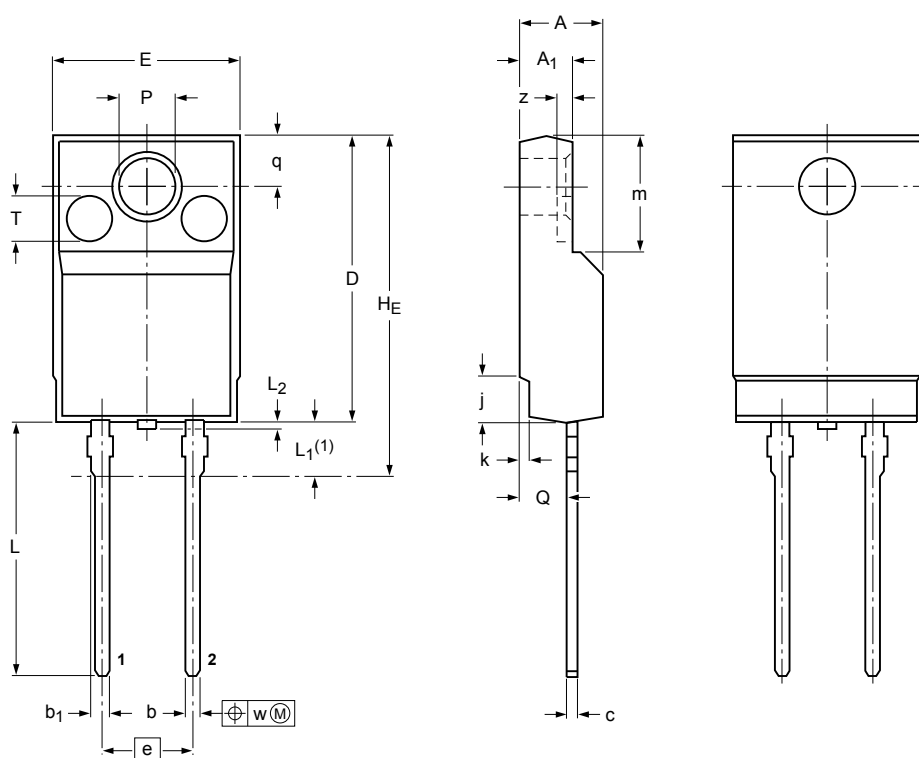
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12. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 2-lead TO-220 'full pack'

SOD113



0 10 20 mm
scale

z(2)
0.8

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	E	e	H _E max	j	k	L	L ₁ (1)	L ₂ max	m	P	Q	q	T	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	0.7 0.4	15.8 15.2	10.3 9.7	5.08	19.0	2.7 1.7	0.6 0.4	14.4 13.5	3.3 2.8	0.5	6.5 6.3	3.2 3.0	2.6 2.3	2.6	2.55	0.4

Notes

1. Terminals are uncontrolled within zone L₁.
2. z is depth of T.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD113		2-lead TO-220F				02-04-09 07-06-18

Fig. 8. Package outline TO-220F (SOD113)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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Date of release: 4 February 2013